

ISO7041 Ultra-Low Power Four-Channel Digital Isolator

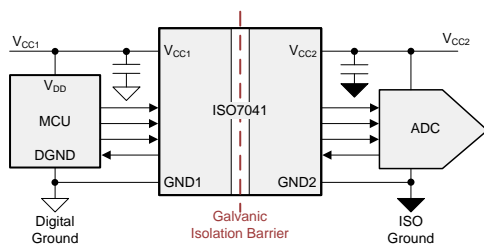
1 Features

- Ultra-Low Power Consumption
 - 4.4 μA per Channel Quiescent Current (3.3 V)
 - 16 μA per Channel at 100 kbps (3.3 V)
 - 126 μA per Channel at 1 Mbps (3.3 V)
- Robust Isolation Barrier
 - >100-Year Projected Lifetime
 - 3000 V_{RMS} Isolation Rating
 - $\pm 100 \text{ kV}/\mu\text{s}$ Typical CMTI
- Wide Supply Range: 2.25 V to 3.63 V
- Wide Temperature Range: -40°C to $+125^{\circ}\text{C}$
- Small 16-QSOP Package (16-DBQ)
- Signaling Rate: Up to 2 Mbps
- Default Output *High* (ISO7041) and *Low* (ISO7041F) Options
- Robust Electromagnetic Compatibility (EMC)
 - System-Level ESD, EFT, and Surge Immunity
 - Very Low Emissions
- Safety-Related Certifications (Planned):
 - UL 1577 Component Recognition Program
 - DIN V VDE V 0884-11
 - CQC, TUV and CSA Certifications
 - IECEx (IEC 60079-0 & IEC 60079-11) and ATEX (EN 60079-11)

2 Applications

- 4-mA to 20-mA Loop Powered Field Transmitters
- Factory Automation, Process Automation
- Programmable Logic Controller (PLC)
- Low-Power GPIO, UART and SPI Isolation

Simplified Application Schematic



3 Description

The ISO7041 device is an ultra-low power, multichannel digital isolator that can be used to isolate CMOS or LVCMOS digital I/Os. Each isolation channel has a logic input and output buffer separated by a double capacitive silicon dioxide (SiO_2) insulation barrier. Innovative edge based architecture combined with an ON-OFF keying modulation scheme allows these isolators to consume very-low power while meeting 3000- V_{RMS} isolation rating per UL1577. The per channel dynamic current consumption of the device is under 130 $\mu\text{A}/\text{Mbps}$ and the per channel static current consumption is 4.4 μA at 3.3 V.

The device can operate as low as 2.25 V, as high as 3.63 V, and is fully functional with different supply voltages on each side of isolation barrier. The four channel isolator comes in a 16-QSOP package with three forward-direction channels and one reverse-direction channel in a 16-QSOP package. The device has default output high and low options. If the input power or signal is lost, default output is *high* for the ISO7041 device and *low* for the ISO7041F device with the F suffix. See the *Device Functional Modes* section for more information.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
ISO7041	QSOP (16)	4.90 mm x 3.90 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Data Rate vs Power Consumption at 3.3 V

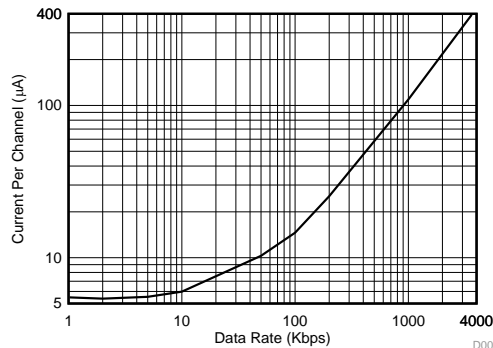


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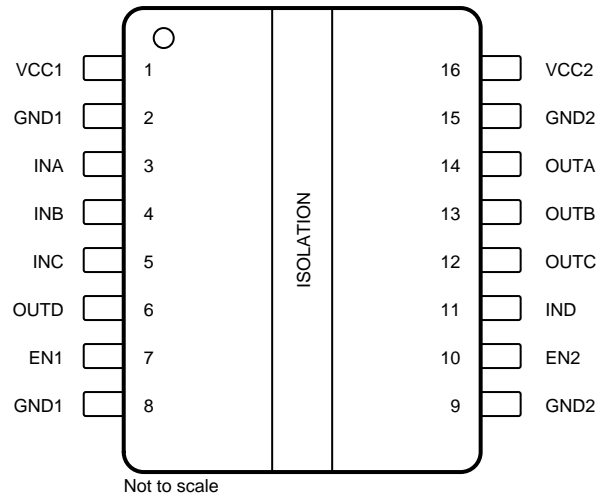
4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
August 2018	*	Initial release.

5 Pin Configuration and Functions

**ISO7041 DBQ Package
16-Pin QSOP
Top View**



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
EN1	7	I	Refresh enable 1. Refresh is enabled when the EN1 pin is connected to GND1. Disable refresh by connecting the EN1 pin high to V_{CC1} . EN1 and EN2 must be connected to the same logic state to enable or disable refresh.
EN2	10	I	Refresh enable 2. Refresh is enabled when the EN2 pin is connected to GND2. Disable refresh by connecting the EN2 pin high to V_{CC2} . EN1 and EN2 must be connected to the same logic state to enable or disable refresh.
GND1	2	—	Ground connection for V_{CC1}
	8		
GND2	9	—	Ground connection for V_{CC2}
	15		
INA	3	I	Input, channel A
INB	4	I	Input, channel B
INC	5	I	Input, channel C
IND	11	I	Input, channel D
OUTA	14	O	Output, channel A
OUTB	13	O	Output, channel B
OUTC	12	O	Output, channel C
OUTD	6	O	Output, channel D
V_{CC1}	1	—	Power supply, side 1
V_{CC2}	16	—	Power supply, side 2

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)^{(1) (2) (3)}

		MIN	MAX	UNIT
Supply Voltage	V _{CC1} to GND1	-0.5	6	V
	V _{CC2} to GND2	-0.5	6	
Input/Output Voltage	INx to GNDx	-0.5	V _{CCX} + 0.5	V
	OUTx to GNDx	-0.5	V _{CCX} + 0.5	
	ENx to GNDx	-0.5	V _{CCX} + 0.5	
Output Current	I _O	-15	15	mA
Temperature	Operating junction temperature, T _J	-40	150	°C
	Storage temperature, T _{stg}	-65	150	°C

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values except differential I/O bus voltages are with respect to the local ground terminal (GND1 or GND2) and are peak voltage values
- (3) Maximum voltage must not exceed 6 V.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±6000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _{CC1} ⁽¹⁾	Supply Voltage Side 1		2.25		3.63	V
V _{CC2} ⁽¹⁾	Supply Voltage Side 2		2.25		3.63	V
V _{IH}	High level Input voltage		0.7 x V _{CCI}		V _{CCI}	V
V _{IL}	Low level Input voltage		0		0.3 x V _{CCI}	V
I _{OH}	High level output current	V _{CCO} = 3.3 V	-2			mA
		V _{CCO} = 2.5 V	-1			mA
I _{OL}	Low level output current	V _{CCO} = 3.3 V			2	mA
		V _{CCO} = 2.5 V			1	mA
DR	Data Rate		0		2	Mbps
T _A	Ambient temperature		-40		125	°C

- (1) V_{CC1} and V_{CC2} can be set independent of one another

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		ISO7041	UNIT
		DBQ (SOIC)	
		16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	87.0	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics application report](#).

Thermal Information (continued)

THERMAL METRIC ⁽¹⁾		ISO7041	UNIT
		DBQ (SOIC)	
		16 PINS	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	33.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	49.1	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	8.4	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	48.5	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	—	°C/W

6.5 Power Ratings

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_D	Maximum power dissipation (both sides)	$V_{CC1} = V_{CC2} = 3.63\text{ V}$, $T_J = 150^\circ\text{C}$, $C_L = 15\text{ pF}$, Input a 1-MHz 50% duty cycle square wave			TBD	mW
P_{D1}	Maximum power dissipation (side-1)				TBD	mW
P_{D2}	Maximum power dissipation (side-2)				TBD	mW

6.6 Insulation Specifications

PARAMETER		TEST CONDITIONS	SPECIFICATIONS	UNIT
			QSOP-16	
IEC 60664-1				
CLR	External clearance ⁽¹⁾	Side 1 to side 2 distance through air	>3.7	mm
CPG	External Creepage ⁽¹⁾	Side 1 to side 2 distance across package surface	>3.7	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	17	μm
CTI	Comparative tracking index	IEC 60112; UL 746A	>600	V
	Material Group	According to IEC 60664-1	I	
	Overvoltage category	Rated mains voltage ≤ 600 V _{RMS}	I-IV	
DIN V VDE V 0884-11:2017-01				
V _{IORM}	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	566	V _{PK}
V _{IOWM}	Maximum isolation working voltage	AC voltage (sine wave); time-dependent dielectric breakdown (TDDb) test; See Figure 10	400	V _{RMS}
		DC voltage	566	V _{DC}
V _{IOTM}	Maximum transient isolation voltage	V _{TEST} = V _{IOTM} , t = 60 s (qualification); V _{TEST} = 1.2 × V _{IOTM} , t = 1 s (100% production)	4242	V _{PK}
V _{IOSM}	Maximum surge isolation voltage	Test method per IEC 62368-1, 1.2/50 μs waveform, V _{TEST} = 1.6 × V _{IOSM} = 6400 V _{PK} (qualification)	4000	V _{PK}
q _{pd}	Apparent charge ⁽²⁾	Method a: After I/O safety test subgroup 2/3, V _{ini} = V _{IOTM} , t _{ini} = 60 s; V _{pd(m)} = 1.2 × V _{IORM} , t _m = 10 s	≤ 5	pC
		Method a: After environmental tests subgroup 1, V _{ini} = V _{IOTM} , t _{ini} = 60 s; V _{pd(m)} = 1.6 × V _{IORM} , t _m = 10 s	≤ 5	
		Method b1: At routine test (100% production) and preconditioning (type test), V _{ini} = V _{IOTM} , t _{ini} = 1 s; V _{pd(m)} = 1.875 × V _{IORM} , t _m = 1 s	≤ 5	
C _{IO}	Barrier capacitance, input to output ⁽³⁾	V _{IO} = 0.4 × sin (2 πft), f = 1 MHz	1.5	pF
R _{IO}	Insulation resistance, input to output ⁽³⁾	V _{IO} = 500 V, T _A = 25°C	> 10 ¹²	Ω
		V _{IO} = 500 V, 100°C ≤ T _A ≤ 150°C	> 10 ¹¹	
		V _{IO} = 500 V at T _S = 150°C	> 10 ⁹	
	Pollution degree		2	
	Climatic category		40/125/21	
UL 1577				
V _{ISO}	Withstand isolation voltage	V _{TEST} = V _{ISO} , t = 60 s (qualification); V _{TEST} = 1.2 × V _{ISO} , t = 1 s (100% production)	3000	V _{RMS}

- (1) Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance. Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a printed circuit board are used to help increase these specifications.
- (2) Apparent charge is electrical discharge caused by a partial discharge (pd).
- (3) All pins on each side of the barrier tied together creating a two-pin device.

6.7 Safety-Related Certifications

VDE	CSA	UL	CQC	TUV	CSA/Sira
Plan to certify according to DIN V VDE V 0884-11:2017- 01	Plan to certify according to IEC 60950-1, and IEC 60601-1	Plan to certify according to UL 1577 Component Recognition Program	Plan to certify according to GB4943.1-2011	Plan to certify according to EN 61010-1:2010 (3rd Ed) and EN 60950-1:2006/A11:2009/A1: 2010/A12:2011/A2:2013	Plan to certify for use in intrinsic safety (IS) to IS applications under ATEX and IECEx
Maximum transient isolation voltage, 4242 V _{PK} ; Maximum repetitive peak isolation voltage, 566 V _{PK} ; Maximum surge isolation voltage, 4000 V _{PK}	CSA 60950-1-07+A1+A2 and IEC 60950-1 2nd Ed., for pollution degree 2, material group I V _{RMS} basic isolation ----- CSA 60601- 1:14 and IEC 60601-1 Ed. 3.1, 2 MOPP (Means of Patient Protection) TBD maximum working voltage	Single protection, 3000 V _{RMS}	Basic insulation, Altitude ≤ 5000 m, Tropical Climate, 250 V _{RMS} maximum working voltage	3000 V _{RMS} Reinforced insulation per EN 61010-1:2010 (3rd Ed) up to working voltage of 300 V _{RMS} 3000 V _{RMS} Reinforced insulation per EN 60950-1:2006/A11:2009/A1: 2010/A12:2011/A2:2013 up to working voltage of 370 V _{RMS}	ATEX: EN 60079-0:2012+A11:2013 and EN 60079-11:2012 IECEX: IEC 60079-0:2011 (6th Ed) and IEC60079-11:2011 (6th Ed) II 1G Ex ia IIC Ga
Certificate planned	Certificate planned	Certificate planned	Certificate planned	Certificate planned	Certificate planned

6.8 Safety Limiting Values

Safety limiting⁽¹⁾ intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
16-QSOP PACKAGE						
I _S	Safety input, output, or supply current	R _{θJA} = 87°C/W, V _I = 3.6 V, T _J = 150°C, T _A = 25°C			399	mA
		R _{θJA} = 87°C/W, V _I = 2.75 V, T _J = 150°C, T _A = 25°C			522	
P _S	Safety input, output, or total power	R _{θJA} = 87°C/W, T _J = 150°C, T _A = 25°C			1435	mW
T _S	Maximum safety temperature				150	°C

- (1) The maximum safety temperature, T_S, has the same value as the maximum junction temperature, T_J, specified for the device. The I_S and P_S parameters represent the safety current and safety power respectively. The maximum limits of I_S and P_S should not be exceeded. These limits vary with the ambient temperature, T_A.

The junction-to-air thermal resistance, R_{θJA}, in the table is that of a device installed on a high-K test board for leaded surface-mount packages. Use these equations to calculate the value for each parameter:

T_J = T_A + R_{θJA} × P, where P is the power dissipated in the device.

T_{J(max)} = T_S = T_A + R_{θJA} × P_S, where T_{J(max)} is the maximum allowed junction temperature.

P_S = I_S × V_I, where V_I is the maximum input voltage.

6.9 Electrical Characteristics 3.3V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{IT+(IN)}	Rising input switching threshold				0.7 × V _{CCI(1)}	V
V _{IT-(IN)}	Falling input switching threshold		0.3 × V _{CCI}			V
V _{OH}	High-level output voltage	I _{OH} = -2mA	V _{CCO} - 0.3	V _{CCO} - 0.2		V
V _{OL}	Low-level output voltage	I _{OL} = 2mA		0.2	0.3	V
V _{I(HYS)}	Input threshold voltage hysteresis		0.1 × V _{CCI}			V
I _{IH}	High-level input current	V _{IH} = V _{CCI} ⁽¹⁾ at INx			1	μA
I _{IL}	Low-level input current	V _{IL} = 0 V at INx	-1			μA
CMTI	Common mode transient immunity	V _I = V _{CC} or 0 V, V _{CM} = 1200 V	50	100		kV/us

(1) V_{CCI} = Input-side V_{CC}; V_{CCO} = Output-side V_{CC}

Electrical Characteristics 3.3V Supply (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_i	Input Capacitance ⁽²⁾	$V_i = V_{CC}/2 + 0.4 \times \sin(2\pi ft)$, $f = 1$ MHz, $V_{CC} = 3.63$ V		2		pF

(2) Measured from input pin to ground.

6.10 Supply Current Characteristics 3.3V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISO7041						
I_{CC1}	Side 1 Supply Current, Refresh Disabled	DC Signal		5.5	10.5	μ A
		10kbps, No Load		8.3	14.7	μ A
		100kbps, No Load		36.9	51.3	μ A
		1Mbps, No Load		323.4	418.8	μ A
	Side 1 Supply Current, Refresh Enabled	Inputs in Fail safe		7.2	13	μ A
		Inputs in Non-Fail safe		8.4	15.8	μ A
		10kbps, No Load		9.5	16.6	μ A
		100kbps, No Load		36.9	51.3	μ A
		1Mbps, No Load		322.3	418.8	μ A
I_{CC2}	Side 2 Supply Current, Refresh Disabled	DC Signal		9.8	15.9	μ A
		10kbps, No Load		11.6	18.3	μ A
		100kbps, No Load		27.1	38.2	μ A
		1Mbps, No Load		183.7	238.8	μ A
	Side 2 Supply Current, Refresh Enabled	Inputs in Fail safe		10.5	15.9	μ A
		Inputs in Non-Fail safe		10.9	17.8	μ A
		10kbps, No Load		11.7	18.7	μ A
		100kbps, No Load		27.1	38.2	μ A
		1Mbps, No Load		182.6	238.8	μ A
$I_{CC1(ch)} + I_{CC2(ch)}$	Total Supply Current Per Channel, Refresh Disabled	DC Signal		3.8	6.5	μ A
		10kbps, No Load		5.0	8.1	μ A
		100kbps, No Load		16.1	21.5	μ A
		1Mbps, No Load		126.5	156	μ A
	Total Supply Current Per Channel, Refresh Enabled	Inputs in Fail safe		4.4	7.4	μ A
		Inputs in Non-Fail safe		4.8	8.4	μ A
		10kbps, No Load		5.3	8.7	μ A
		100kbps, No Load		16.1	21.5	μ A
		1Mbps, No Load		126.5	156	μ A

6.11 Electrical Characteristics 2.5V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{IT+(IN)}$	Rising input switching threshold				$0.7 \times V_{CCI(1)}$	V
$V_{IT-(IN)}$	Falling input switching threshold		$0.3 \times V_{CCI}$			V
V_{OH}	High-level output voltage	$I_{OH} = -1$ mA	$V_{CCO} - 0.2$			V
V_{OL}	Low-level output voltage	$I_{OL} = 1$ mA			0.2	V
$V_{I(HYS)}$	Input threshold voltage hysteresis		$0.1 \times V_{CCI}$			V

(1) V_{CCI} = Input-side V_{CC} ; V_{CCO} = Output-side V_{CC}

Electrical Characteristics 2.5V Supply (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{IH}	High-level input current	$V_{IH} = V_{CCI}^{(1)}$ at INx			1	μA
I_{IL}	Low-level input current	$V_{IL} = 0 V$ at INx	-1			μA
CMTI	Common mode transient immunity	$V_I = V_{CC}$ or 0 V, $V_{CM} = 1200 V$	50	100		kV/us
C_i	Input Capacitance ⁽²⁾	$V_I = V_{CC}/2 + 0.4 \times \sin(2\pi ft)$, $f = 1 MHz$, $V_{CC} = 2.5 V$		2		pF

(2) Measured from input pin to ground.

6.12 Supply Current Characteristics 2.5V Supply

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ISO7041						
I_{CC1}	Side 1 Supply Current, Refresh Disabled	DC Signal		5.1	9.3	μA
		10kbps, No Load		8.6	13.2	μA
		100kbps, No Load		35.6	47.1	μA
		1Mbps, No Load		306.9	387.6	μA
	Side 1 Supply Current, Refresh Enabled	Inputs in Fail safe		6.7	11.7	μA
		Inputs in Non-Fail safe		7.9	14.1	μA
		10kbps, No Load		8.7	15.2	μA
		100kbps, No Load		35.6	47.1	μA
		1Mbps, No Load		305.8	387.6	μA
	Side 2 Supply Current, Refresh Disabled	DC Signal		9.4	14.8	μA
		10kbps, No Load		11.1	17.0	μA
		100kbps, No Load		25.1	34.9	μA
		1Mbps, No Load		167.2	216	μA
		Inputs in Fail safe		10.0	14.8	μA
		Inputs in Non-Fail safe		10.5	16.6	μA
		10kbps, No Load		11.1	18.3	μA
		100kbps, No Load		25.1	34.9	μA
$I_{CC1(ch)} + I_{CC2(ch)}$	Total Supply Current Per Channel, Refresh Disabled	DC Signal		3.6	6.0	μA
		10kbps, No Load		4.8	7.4	μA
		100kbps, No Load		15.0	19.5	μA
		1Mbps, No Load		118.8	141.6	μA
	Total Supply Current Per Channel, Refresh Enabled	Inputs in Fail safe		4.2	6.8	μA
		Inputs in Non-Fail safe		4.6	7.6	μA
		10kbps, No Load		4.9	8.2	μA
		100kbps, No Load		15.0	19.5	μA
		1Mbps, No Load		117.7	141.6	μA
		DC Signal		3.6	6.0	μA
		10kbps, No Load		4.8	7.4	μA
		100kbps, No Load		15.0	19.5	μA

6.13 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

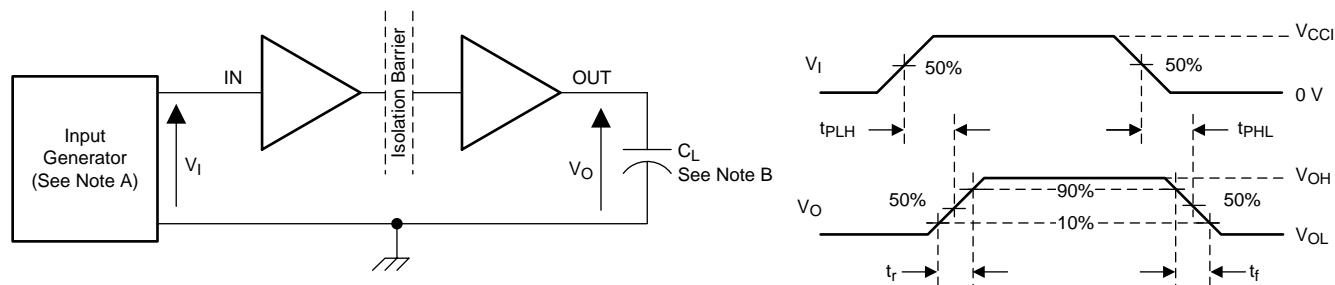
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} , t_{PHL}	Propagation delay time	See Figure 1		140	175	ns
t_{UI}	Minimum pulse width		500			ns
PWD	Pulse width distortion				10	ns

Switching Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

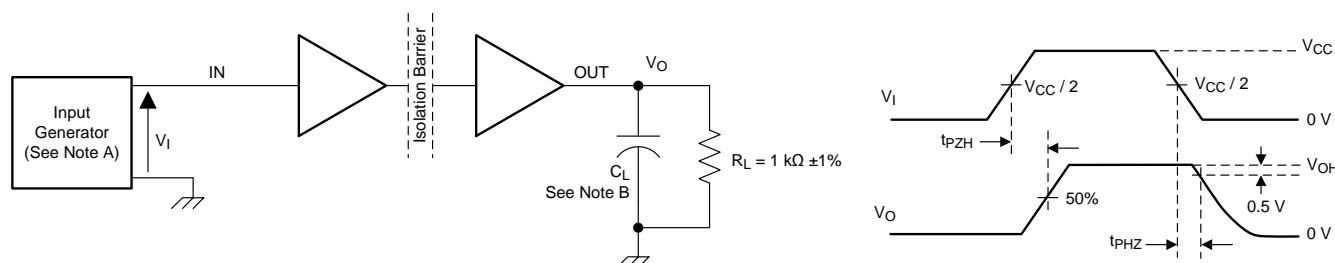
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{sk(o)}$	Channel to channel output skew time	Same-direction channels			10	ns
		Opposite-direction channels			10	ns
$t_{sk(p-p)}$	Part to part skew time				70	ns
t_R	Output signal rise time	See Figure 1			5	ns
t_F	Output signal fall time				5	ns
t_{DO}	Default output delay time from input power loss	Refresh enabled, See Figure 3		400	750	us
t_{PU}	Time from UVLO to valid output data		1		5	ms
F_R	Refresh rate		5	10		kbps

7 Parameter Measurement Information



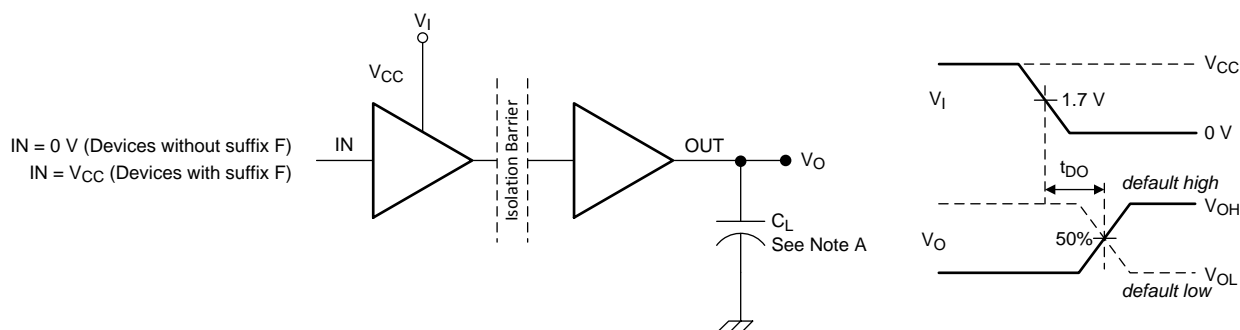
- The input pulse is supplied by a generator having the following characteristics: $PRR \leq 50$ kHz, 50% duty cycle, $t_r \leq 3$ ns, $t_f \leq 3$ ns, $Z_O = 50 \Omega$. At the input, 50Ω resistor is required to terminate Input Generator signal. It is not needed in actual application.
- $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 1. Switching Characteristics Test Circuit and Voltage Waveforms



- The input pulse is supplied by a generator having the following characteristics: $PRR \leq 10$ kHz, 50% duty cycle, $t_r \leq 3$ ns, $t_f \leq 3$ ns.
- $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

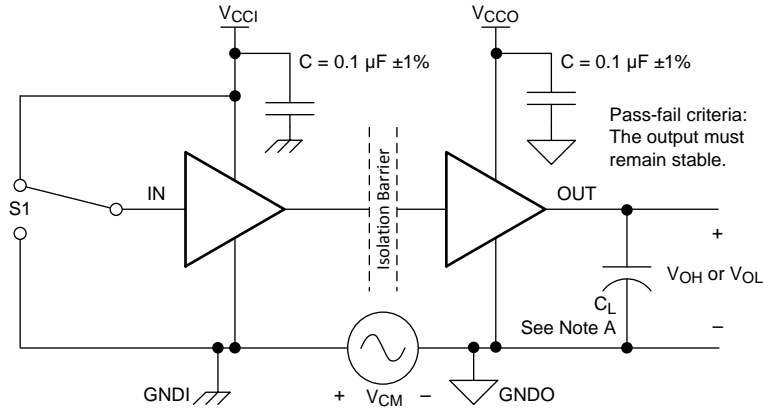
Figure 2. Propagation Delay Time Test Circuit and Waveform



- $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.
- Power Supply Ramp Rate = 10 mV/ns

Figure 3. Default Output Delay Time Test Circuit and Voltage Waveforms

Parameter Measurement Information (continued)



- A. $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 4. Common-Mode Transient Immunity Test Circuit

8 Detailed Description

8.1 Overview

The ISO7041 device uses edge encoding of data with an ON-OFF keying (OOK) modulation scheme to transmit the digital data across a silicon dioxide isolation barrier. The transmitter uses a high frequency carrier signal to pass data across the barrier representing a signal edge transition. Using this method achieves very low power consumption and high immunity. The receiver demodulates the carrier signal after advanced signal conditioning and produces the output through a buffer stage. For low data rates, a refresh logic option is available to make sure the output state matches the input state. The ENx pins of side A and side B must be tied low to enable refresh or high to disable refresh. Advanced circuit techniques are used to maximize the CMTI performance and minimize the radiated emissions due the high frequency carrier and IO buffer switching. The conceptual block diagram of a digital capacitive isolator, [Figure 5](#), shows a functional block diagram of a typical channel.

8.2 Functional Block Diagram

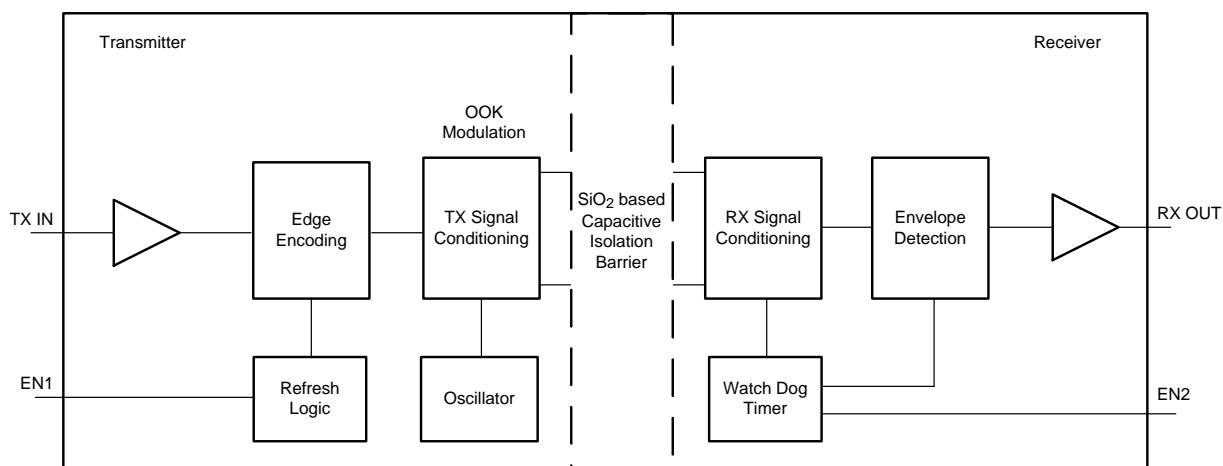


Figure 5. Conceptual Block Diagram of a Digital Capacitive Isolator

8.3 Feature Description

[Table 1](#) shows an overview of the device features.

Table 1. Device Features

PART NUMBER	CHANNEL DIRECTION	MAXIMUM DATA RATE	DEFAULT OUTPUT	PACKAGE	RATED ISOLATION ⁽¹⁾
ISO7041	3 Forward, 1 Reverse	2 Mbps	High	DBQ-16	3000 V _{RMS} / 4242 V _{PK}
ISO7041 with F suffix	3 Forward, 1 Reverse	2 Mbps	Low	DBQ-16	3000 V _{RMS} / 4242 V _{PK}

(1) See for detailed isolation ratings.

8.3.1 Refresh Enable

The ISO7041 uses an edge based encoding scheme to transfer an input signal change across the isolation barrier versus sending across the DC state. Enabling the refresh feature consistently validates that the DC output state of each isolator channel matches the DC input state. An internal watchdog timer monitors for activity on the individual inputs and transmits the logic state when there is no input signal transition for more than 100 μ s. This ensures that the input and output state of the isolator always match. Tie both EN1 and EN2 to their respective grounds to enable refresh.

Disable refresh by tying both EN1 and EN2 to their respective VCC power supplies. Disabling refresh will further decrease the power consumption of the device but the DC state is not guaranteed at startup. System level solutions can be implemented to ensure the isolator channel output matches the input at startup. For example, at start up, an immediate full transition of the input signals from high to low and low to high on the individual isolator lines would allow the states of the outputs to properly track the inputs.

8.3.2 Electromagnetic Compatibility (EMC) Considerations

Many applications in harsh industrial environment are sensitive to disturbances such as electrostatic discharge (ESD), electrical fast transient (EFT), surge and electromagnetic emissions. These electromagnetic disturbances are regulated by international standards such as IEC 61000-4-x and CISPR 22. Although system-level performance and reliability depends, to a large extent, on the application board design and layout, the ISO70xx family of devices incorporates many chip-level design improvements for overall system robustness. Some of these improvements include:

- Robust ESD protection cells for input and output signal pins and inter-chip bond pads.
- Low-resistance connectivity of ESD cells to supply and ground pins.
- Enhanced performance of high voltage isolation capacitor for better tolerance of ESD, EFT and surge events.
- Bigger on-chip decoupling capacitors to bypass undesirable high energy signals through a low impedance path.
- PMOS and NMOS devices isolated from each other by using guard rings to avoid triggering of parasitic SCRs.
- Reduced common mode currents across the isolation barrier by ensuring purely differential internal operation.

The device has no issue being able to meet either CISPR 22 Class A and CISPR22 Class B standards in an unshielded environment.

8.4 Device Functional Modes

Table 2 shows the functional modes for the device.

Table 2. Function Table⁽¹⁾

V _{CCI}	V _{CCO}	INPUT (INx) ⁽²⁾	REFRESH ENABLE (ENx)	OUTPUT (OUTx)	COMMENTS
PU	PU	H	L	H	Normal Operation: A channel output assumes the logic state of its input.
		L	L	L	
		X	H	Undetermined	The device needs an input signal transition to validate the output tracks the input state. Without a signal edge transition, the output will be in an undetermined state.
PD	PU	X	L	Default	When V _{CCI} is unpowered, a channel output assumes the logic state based on the selected default option. Default is <i>High</i> for the device without the F suffix and <i>Low</i> for device with the F suffix. When V _{CCI} transitions from unpowered to powered-up, a channel output assumes the logic state of the input. When V _{CCI} transitions from powered-up to unpowered, channel output assumes the selected default state.
			H	Undetermined	When V _{CCI} is unpowered, a channel output assumes the logic state based on the previous state of the output before V _{CCI} powered down.
X	PD	X	L	Undetermined	When V _{CCO} is unpowered, a channel output is undetermined ⁽³⁾ . When V _{CCO} transitions from unpowered to powered-up, a channel output assumes the logic state of the input.
			H	Undetermined	When V _{CCO} is unpowered, a channel output is undetermined ⁽³⁾ . When V _{CCO} transitions from unpowered to powered-up, a channel output assumes the selected default option.
X	X	X	Open	Undetermined	When ENx is unconnected or open, the device output will be in an undetermined and unknown state. ENx must be connected high or low for the device to behave correctly.

(1) V_{CCI} = Input-side V_{CC}; V_{CCO} = Output-side V_{CC}; PU = Powered up (V_{CC} ≥ 2.25 V); PD = Powered down (V_{CC} ≤ 1.54); X = Irrelevant; H = High level; L = Low level ; Z = High Impedance

(2) A strongly driven input signal can weakly power the floating V_{CC} through an internal protection diode and cause undetermined output.

(3) The outputs are in undetermined state when 2.25 V < V_{CCI}, V_{CCO} < 2.25 V.

8.4.1 Device I/O Schematics

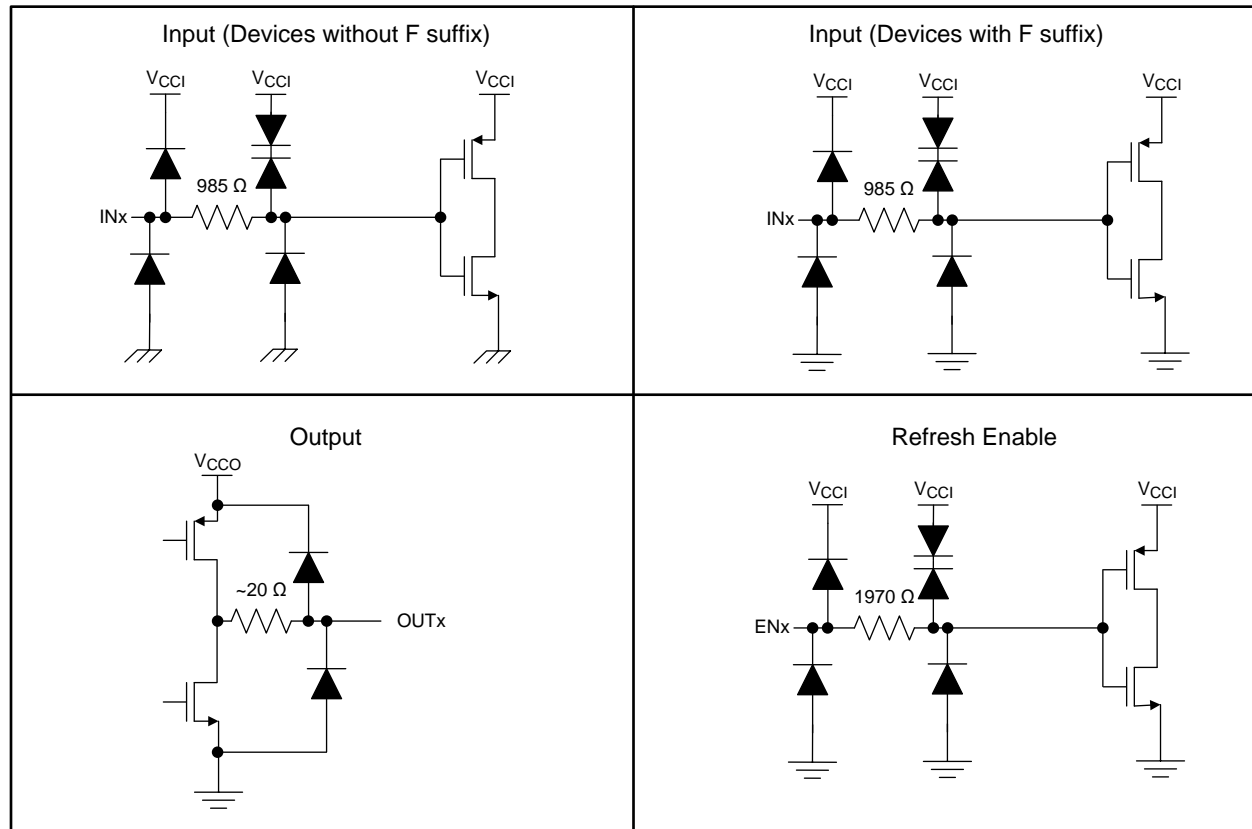


Figure 6. Device I/O Schematics

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

The ISO7041 device is an ultra-low power digital isolator. The device uses single-ended CMOS-logic switching technology. The voltage range is from 2.25 V to 3.63 V for both supplies, V_{CC1} and V_{CC2} , and can be set irrespective of one another. When designing with digital isolators, keep in mind that because of the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (that is, μC or UART), and a data converter or a line transceiver, regardless of the interface type or standard.

9.2 Typical Application

Figure 7 shows the isolated serial peripheral interface (SPI).

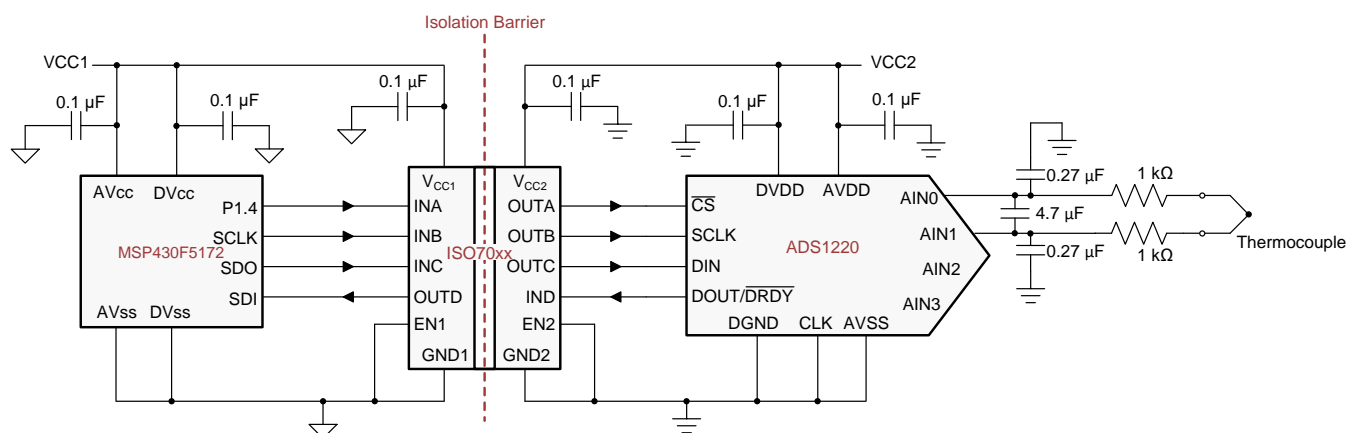


Figure 7. Isolated SPI for a Temperature Field Transmitter

Typical Application (continued)

9.2.1 Design Requirements

To design with these devices, use the parameters listed in [Table 3](#).

Table 3. Design Parameters

PARAMETER	VALUE
Supply voltage, V_{CC1} and V_{CC2}	2.25 V to 3.63 V
Decoupling capacitor between V_{CC1} and GND1	0.1 μ F
Decoupling capacitor from V_{CC2} and GND2	0.1 μ F

9.2.2 Detailed Design Procedure

Unlike optocouplers, which require external components to improve performance, provide bias, or limit current, the device only require two external bypass capacitors to operate.

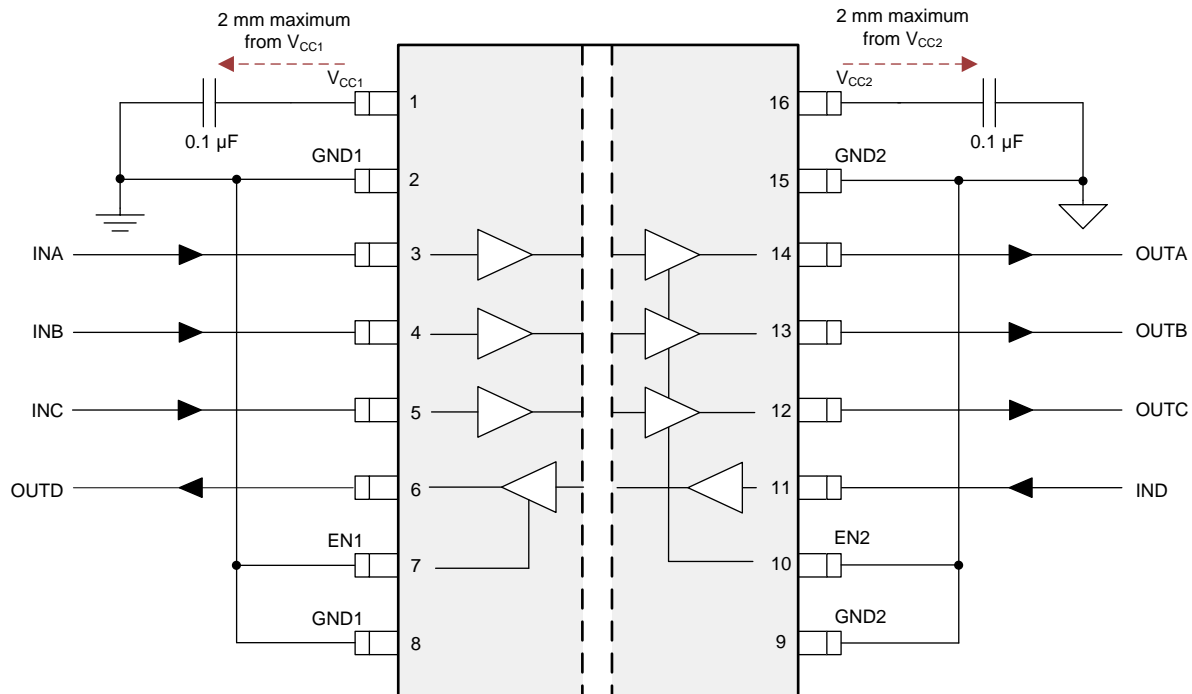


Figure 8. Typical ISO7041 Circuit Hook-up

9.2.3 Insulation Lifetime

Insulation lifetime projection data is collected by using industry-standard Time Dependent Dielectric Breakdown (TDDB) test method. In this test, all pins on each side of the barrier are tied together creating a two-terminal device and high voltage applied between the two sides; see [Figure 9](#) for TDDB test setup. The insulation breakdown data is collected at various high voltages switching at 60 Hz over temperature. For reinforced insulation, VDE standard requires the use of TDDB projection line with failure rate of less than 1 part per million (ppm) and a minimum insulation lifetime of 20 years. VDE standard also requires additional safety margin of 20% for working voltage and 87.5% for insulation lifetime which translates into minimum required life time of 37.5 years.

Figure 10 shows the intrinsic capability of the isolation barrier to withstand high voltage stress over its lifetime. Based on the TDDB data, the intrinsic capability of these devices is 400 VRMS with a lifetime of >100 years. Other factors, such as package size, pollution degree, material group, etc. can further limit the working voltage of the component. The working voltage of the DBQ-16 package specified up to 400 VRMS. At the lower working voltages, the corresponding insulation barrier life time is much longer.

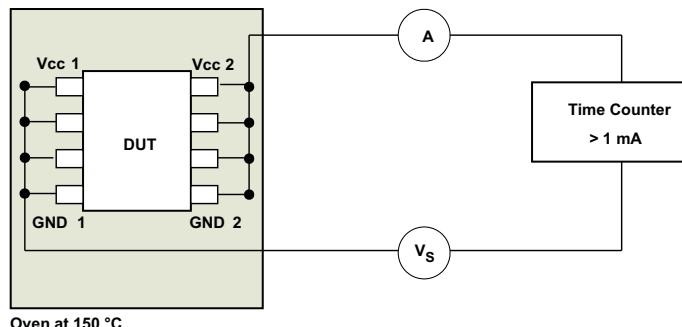


Figure 9. Test Setup for Insulation Lifetime Measurement

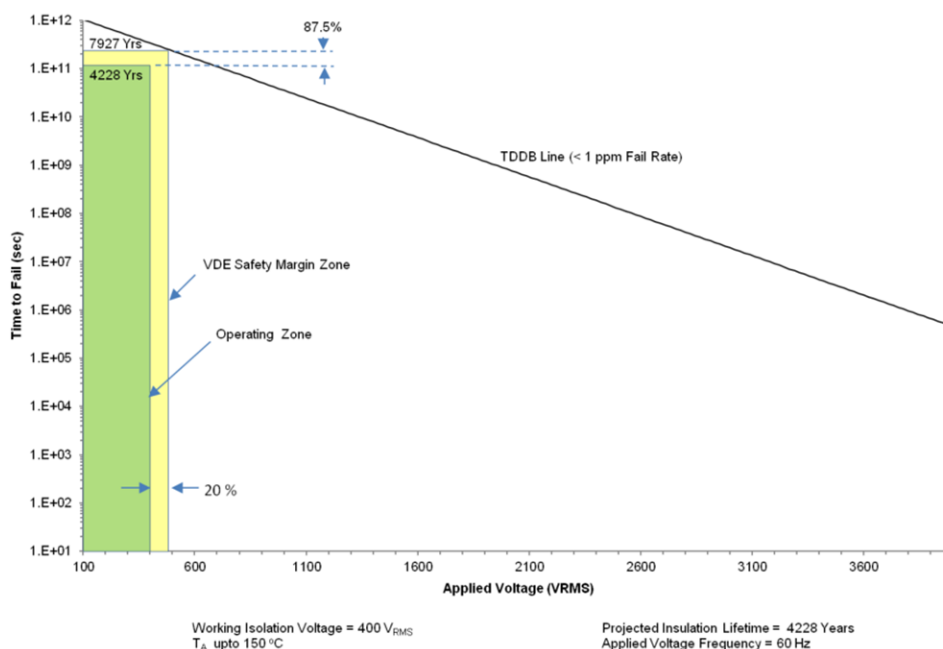


Figure 10. Insulation Lifetime Projection Data

10 Power Supply Recommendations

Put a 0.1-μF bypass capacitor at the input and output supply pins (V_{CC1} and V_{CC2}) to make sure that operation is reliable at data rates and supply voltage. Put the capacitors as near to the supply pins as possible. If only one primary-side power supply is available in an application, use a transformer driver to help generate the isolated power for the secondary-side. Texas Instruments recommends the [SN6501](#) device or [SN6505A](#) device. Refer to the [SN6501 Transformer Driver for Isolated Power Supplies data sheet](#) or [SN6505 Low-Noise 1-A Transformer Drivers for Isolated Power Supplies data sheet](#) for detailed power supply design and transformer selection recommendations.

11 Layout

11.1 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see [Figure 11](#)). Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100 pF/in².
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

If an additional supply voltage plane or signal layer is needed, add a second power or ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

Refer to the [Digital Isolator Design Guide](#) for detailed layout recommendations,.

11.1.1 PCB Material

For digital circuit boards operating at less than 150 Mbps, (or rise and fall times greater than 1 ns), and trace lengths of up to 10 inches, use standard FR-4 UL94V-0 printed circuit board. This PCB is preferred over cheaper alternatives because of lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and the self-extinguishing flammability-characteristics.

11.2 Layout Example

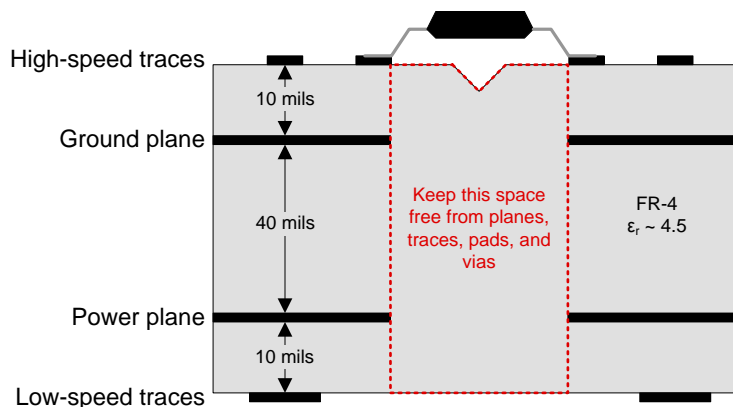


Figure 11. Recommended Layer Stack

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [Digital Isolator Design Guide](#)
- Texas Instruments, [Isolation Glossary](#)
- Texas Instruments, [ADS1220 4-Channel, 2-kSPS, Low-Power, 24-Bit ADC with Integrated PGA and Reference data sheet](#)
- Texas Instruments, [ADS122U04 24-Bit, 4-Channel, 2-kSPS, Delta-Sigma ADC With UART Interface data sheet](#)
- Texas Instruments, [ADS124S0x Low-Power, Low-Noise, Highly Integrated, 6- and 12-Channel, 4-kSPS, 24-Bit, Delta-Sigma ADC with PGA and Voltage Reference data sheet](#)
- Texas Instruments, [Uniquely Efficient Isolated DC/DC Converter for Ultra-Low Power and Low-Power Applications TI Design](#)
- Texas Instruments, [SN6501 Transformer Driver for Isolated Power Supplies data sheet](#)
- Texas Instruments, [SN6505A Low-Noise 1-A Transformer Drivers for Isolated Power Supplies data sheet](#)

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Community Resource

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

E2E is a trademark of Texas Instruments.

12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ISO7041DBQ	PREVIEW	SSOP	DBQ	16	1500	TBD	Call TI	Call TI	-40 to 125		
ISO7041DBQR	PREVIEW	SSOP	DBQ	16	2500	TBD	Call TI	Call TI	-40 to 125		
ISO7041FDBQ	PREVIEW	SSOP	DBQ	16	1500	TBD	Call TI	Call TI	-40 to 125		
ISO7041FDBQR	PREVIEW	SSOP	DBQ	16	2500	TBD	Call TI	Call TI	-40 to 125		
XISO7041DBQR	ACTIVE	SSOP	DBQ	16	2500	TBD	Call TI	Call TI	-40 to 125		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

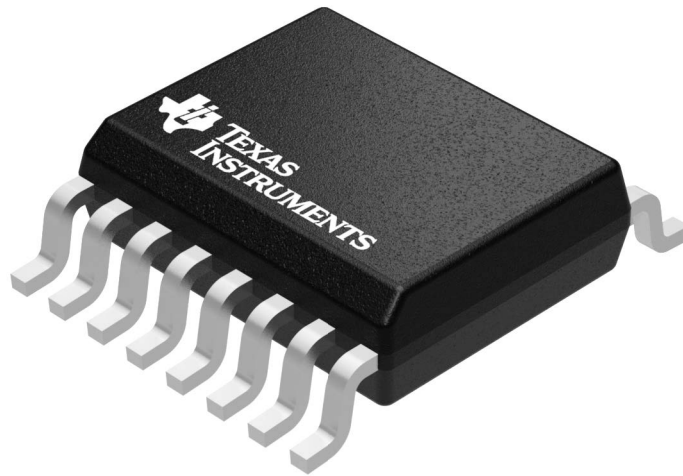
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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